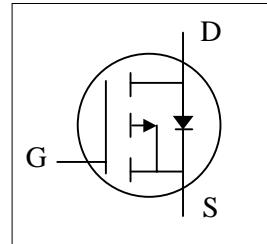




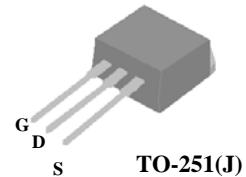
- ▼ Lower On-resistance
- ▼ Simple Drive Requirement
- ▼ Fast Switching Characteristic



$BV_{DSS}$	-60V
$R_{DS(ON)}$	160m $\Omega$
$I_D$	-10A

## Description

The TO-252 package is widely preferred for all commercial-industrial surface mount applications and suited for low voltage applications such as DC/DC converters. The through-hole version (AP9578GJ) is available for low-profile applications.



## Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
$V_{DS}$	Drain-Source Voltage	-60	V
$V_{GS}$	Gate-Source Voltage	$\pm 25$	V
$I_D @ T_C = 25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-10	A
$I_D @ T_C = 100^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10\text{V}$	-6	A
$I_{DM}$	Pulsed Drain Current <sup>1</sup>	-45	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation	28	W
	Linear Derating Factor	0.23	W/ $^\circ\text{C}$
$T_{STG}$	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

## Thermal Data

Symbol	Parameter	Value	Units
$R_{thj-c}$	Maximum Thermal Resistance, Junction-case	4.5	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient (PCB mount) <sup>3</sup>	62.5	$^\circ\text{C}/\text{W}$
$R_{thj-a}$	Maximum Thermal Resistance, Junction-ambient	110	$^\circ\text{C}/\text{W}$



## Electrical Characteristics@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$\text{BV}_{\text{DSS}}$	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=-250\mu\text{A}$	-60	-	-	V
$\Delta \text{BV}_{\text{DSS}}/\Delta T_j$	Breakdown Voltage Temperature Coefficient	Reference to $25^\circ\text{C}$ , $I_{\text{D}}=-1\text{mA}$	-	-0.06	-	$\text{V}/^\circ\text{C}$
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance <sup>2</sup>	$V_{\text{GS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	-	160	$\text{m}\Omega$
		$V_{\text{GS}}=-4.5\text{V}, I_{\text{D}}=-3\text{A}$	-	-	200	$\text{m}\Omega$
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=-250\mu\text{A}$	-1	-	-3	V
$g_{\text{fs}}$	Forward Transconductance	$V_{\text{DS}}=-10\text{V}, I_{\text{D}}=-5\text{A}$	-	6	-	S
$I_{\text{DSS}}$	Drain-Source Leakage Current	$V_{\text{DS}}=-60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-10	$\text{uA}$
	Drain-Source Leakage Current ( $T_j=150^\circ\text{C}$ )	$V_{\text{DS}}=-48\text{V}, V_{\text{GS}}=0\text{V}$	-	-	-25	$\text{uA}$
$I_{\text{GSS}}$	Gate-Source Leakage	$V_{\text{GS}}=\pm 25\text{V}$	-	-	$\pm 100$	nA
$Q_g$	Total Gate Charge <sup>2</sup>	$I_{\text{D}}=-5\text{A}$	-	10	16	nC
$Q_{\text{gs}}$	Gate-Source Charge	$V_{\text{DS}}=-48\text{V}$	-	2	-	nC
$Q_{\text{gd}}$	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=-4.5\text{V}$	-	4	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time <sup>2</sup>	$V_{\text{DS}}=-30\text{V}$	-	10	-	ns
$t_r$	Rise Time	$I_{\text{D}}=-5\text{A}$	-	13	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_G=3.3\Omega, V_{\text{GS}}=-10\text{V}$	-	34	-	ns
$t_f$	Fall Time	$R_D=6\Omega$	-	29	-	ns
$C_{\text{iss}}$	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	760	1220	pF
$C_{\text{oss}}$	Output Capacitance	$V_{\text{DS}}=-25\text{V}$	-	80	-	pF
$C_{\text{rss}}$	Reverse Transfer Capacitance	f=1.0MHz	-	60	-	pF

## Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
$V_{\text{SD}}$	Forward On Voltage <sup>2</sup>	$I_S=-5\text{A}, V_{\text{GS}}=0\text{V}$	-	-	-1.2	V
$t_{\text{rr}}$	Reverse Recovery Time <sup>2</sup>	$I_S=-5\text{A}, V_{\text{GS}}=0\text{V},$	-	45	-	ns
	Reverse Recovery Charge	$dI/dt=-100\text{A}/\mu\text{s}$	-	107	-	nC

## Notes:

- 1.Pulse width limited by safe operating area.
- 2.Pulse test
- 3.Surface mounted on 1 in<sup>2</sup> copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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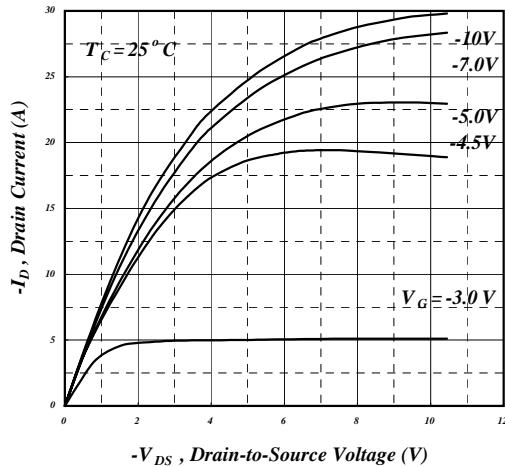


Fig 1. Typical Output Characteristics

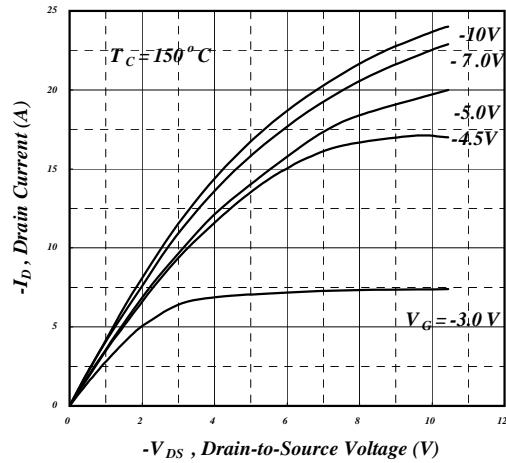


Fig 2. Typical Output Characteristics

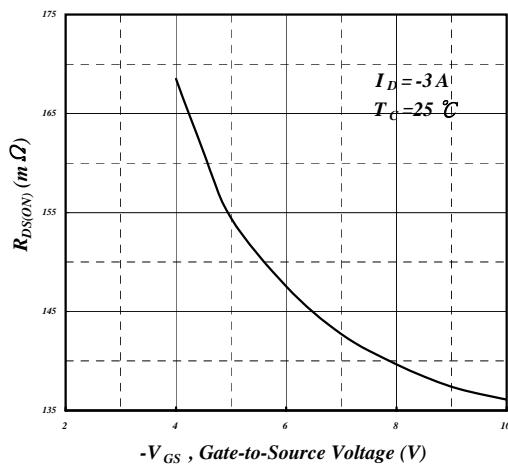


Fig 3. On-Resistance v.s. Gate Voltage

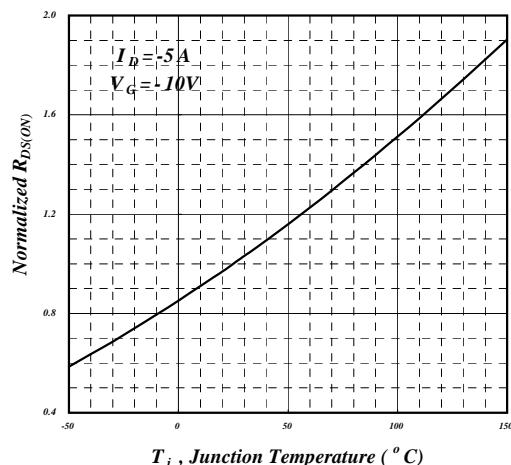


Fig 4. Normalized On-Resistance v.s. Junction Temperature

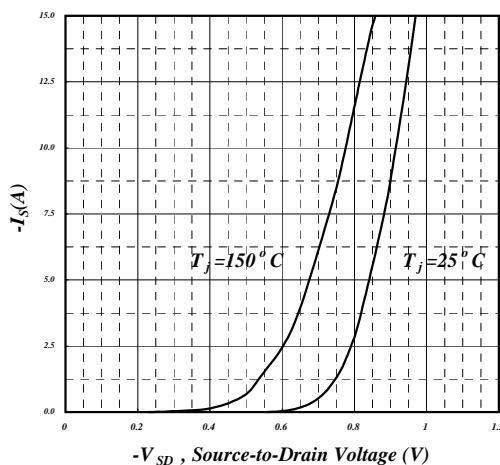


Fig 5. Forward Characteristic of Reverse Diode

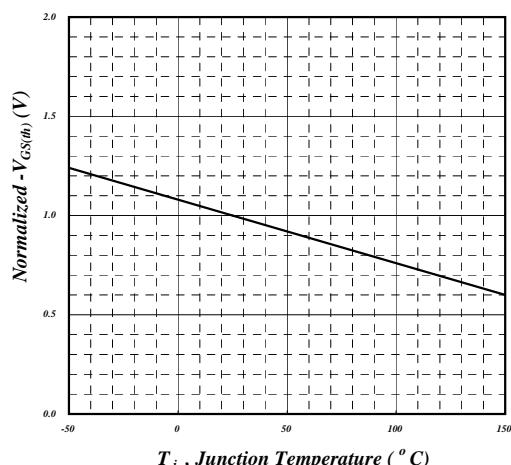
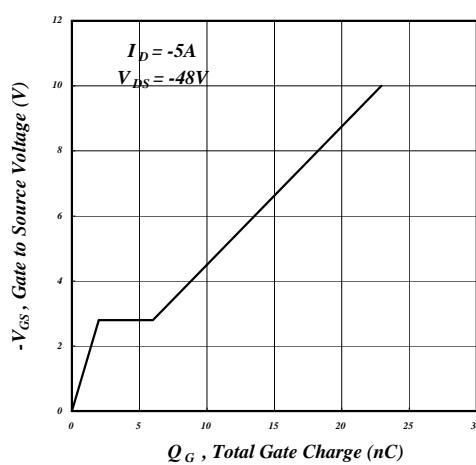
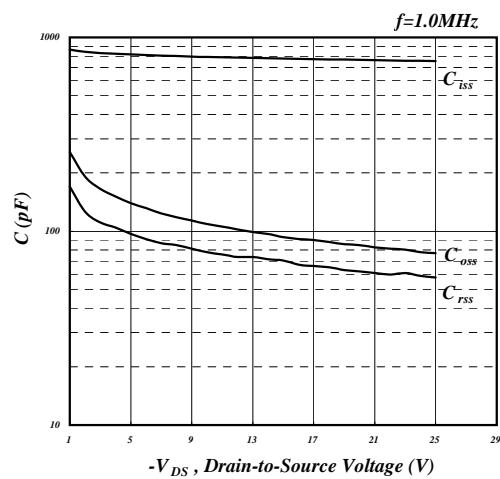


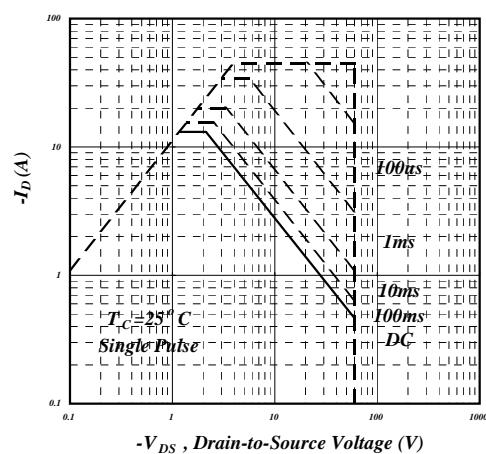
Fig 6. Gate Threshold Voltage v.s. Junction Temperature



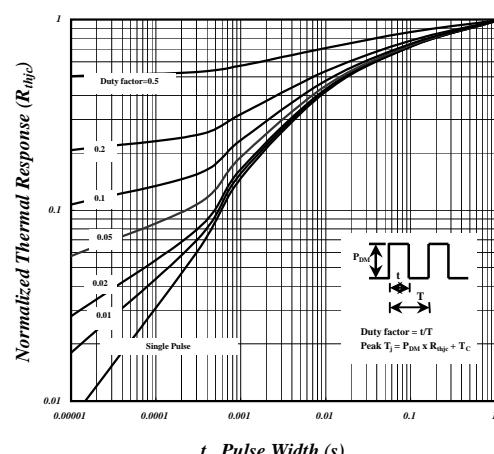
**Fig 7. Gate Charge Characteristics**



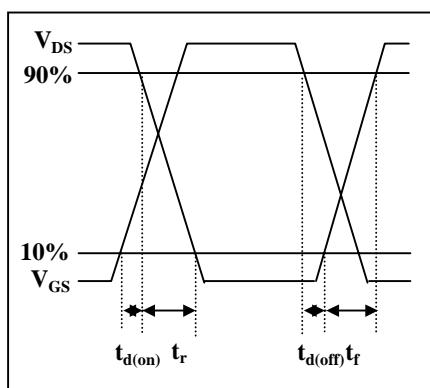
**Fig 8. Typical Capacitance Characteristics**



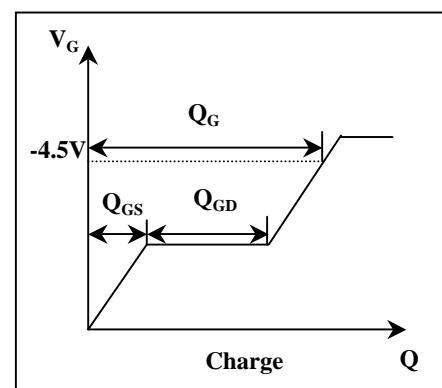
**Fig 9. Maximum Safe Operating Area**



**Fig 10. Effective Transient Thermal Impedance**



**Fig 11. Switching Time Waveform**

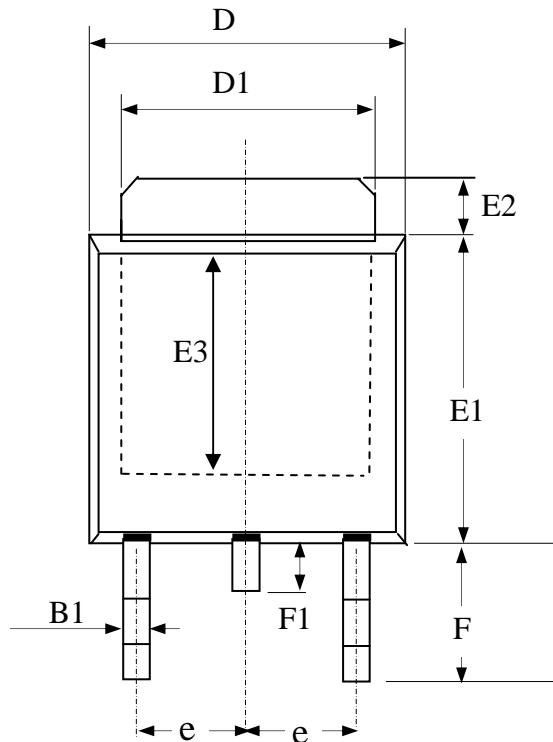


**Fig 12. Gate Charge Waveform**



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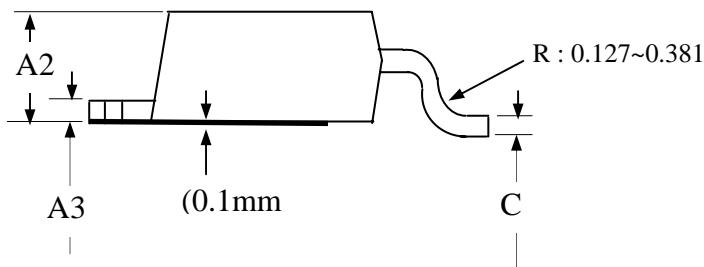
## Package Outline : TO-252



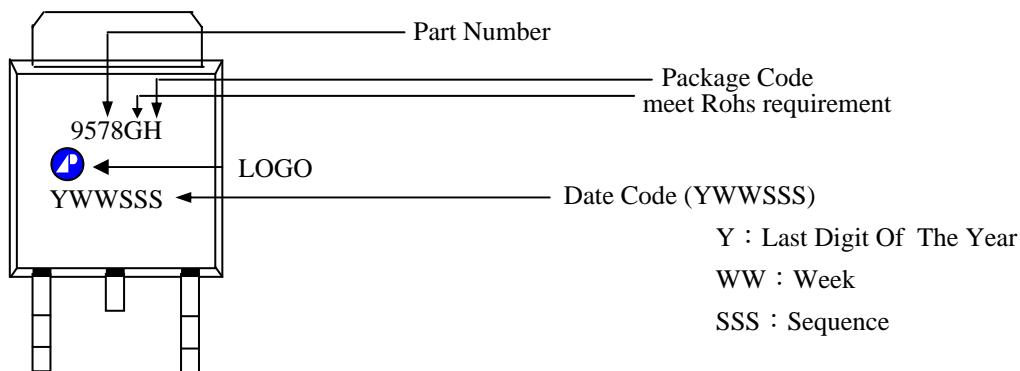
SYMBOLS	Millimeters		
	MIN	NOM	MAX
A2	1.80	2.30	2.80
A3	0.40	0.50	0.60
B1	0.40	0.70	1.00
D	6.00	6.50	7.00
D1	4.80	5.35	5.90
E3	3.50	4.00	4.50
F	2.20	2.63	3.05
F1	0.5	0.85	1.20
E1	5.10	5.70	6.30
E2	0.50	1.10	1.80
e	--	2.30	--
C	0.35	0.50	0.65

1. All Dimensions Are in Millimeters.

2. Dimension Does Not Include Mold Protrusions.

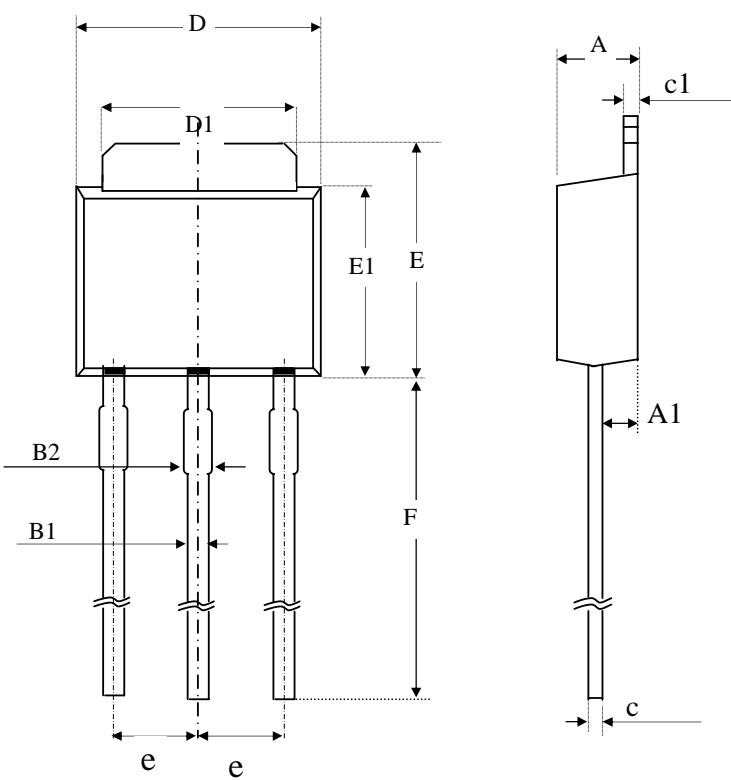


## Part Marking Information & Packing : TO-252





## Package Outline : TO-251



SYMBOLS	Millimeters		
	MIN	NOM	MAX
A	2.20	2.30	2.40
A1	0.90	1.20	1.50
B1	0.50	0.69	0.88
B2	0.60	0.87	1.14
c	0.40	0.50	0.60
c1	0.40	0.50	0.60
D	6.40	6.60	6.80
D1	5.20	5.35	5.50
E	6.70	7.00	7.30
E1	5.40	5.80	6.20
e	----	2.30	----
F	5.88	6.84	7.80

1. All Dimensions Are in Millimeters.

2. Dimension Does Not Include Mold Protrusions.

## Part Marking Information & Packing : TO-251

